

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|-----------------------------------|-----------------|--|------------------|--------------|------|
| Drain-Source Voltage | | | V _{DSS} | 20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Continuous Drain Current (Note 6) | Steady State | T _A = +25°C T _A = +85°C | ID | 5.47 3.43 | А |
| Pulsed Drain Current (Note 7) | | | I _{DM} | 20 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|----------------------------------|-------------|------|
| Power Dissipation (Note 6) | PD | 0.74 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6) | R _{0JA} | 167 | °C/W |
| Operating and Storage Temperature Range | T _{J,} T _{STG} | -55 to +150 | C° |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

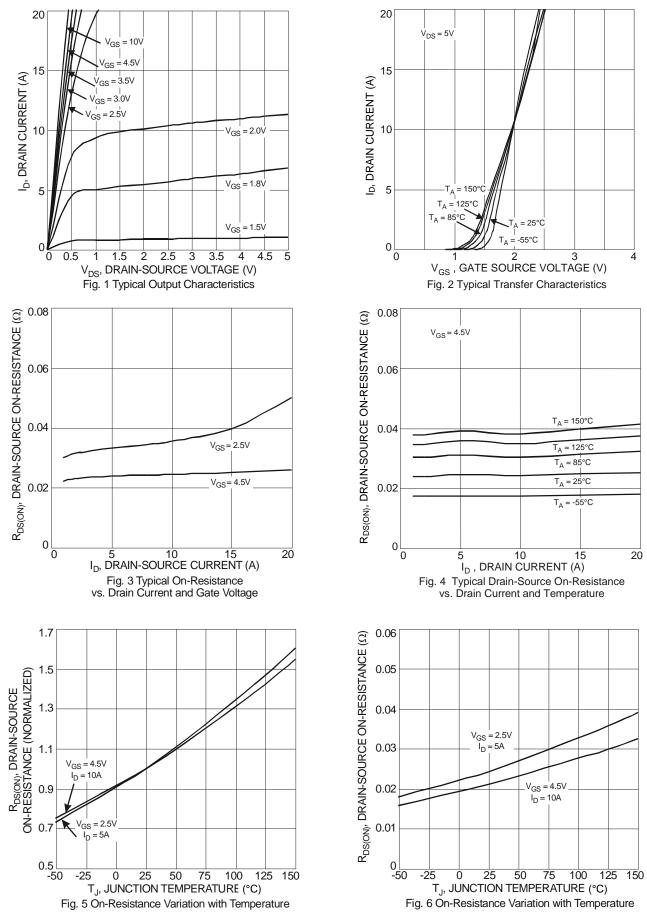
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|-------|-------|------|------|--|--|
| OFF CHARACTERISTICS (Note 8) | Cymbol | WIIII | Typ | Max | Onit | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | _ | | V | $V_{GS} = 0V, I_D = 250 \mu A$ | |
| Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$ | I _{DSS} | | _ | 1.0 | μA | $V_{DS} = 20V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 12V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 8) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.5 | 0.95 | 1.2 | V | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | |
| | | | 21 | 29 | mΩ | $V_{GS} = 10V, I_D = 6A$ | |
| Ctatia Ducia Course On Desintence | | | 25 | 35 | | $V_{GS} = 4.5V, I_D = 5A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | 34 | 48 | | $V_{GS} = 2.5V, I_D = 4A$ | |
| | | | 65 | 91 | | V _{GS} = 1.8V, I _D = 2A | |
| Forward Transfer Admittance | Y _{fs} | _ | 9 | _ | S | V _{DS} = 5V, I _D = 3.8A | |
| Diode Forward Voltage | V _{SD} | _ | 0.75 | 1.0 | V | $V_{GS} = 0V, I_S = 1A$ | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | ÷ | |
| Input Capacitance | Ciss | | 434.7 | _ | pF | $V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz | |
| Output Capacitance | Coss | — | 69.1 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | _ | 61.2 | — | pF | | |
| Gate Resistance | Rg | — | 1.53 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$ | |
| Total Gate Charge | Qg | _ | 5.4 | — | nC | $V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 6A$ | |
| Gate-Source Charge | Q _{gs} | _ | 0.9 | — | nC | | |
| Gate-Drain Charge | Q _{gd} | _ | 1.5 | — | nC | | |
| Turn-On Delay Time | t _{D(ON)} | | 6.5 | | ns | | |
| Turn-On Rise Time | t _R | | 8.3 | | ns | $V_{DD} = 10V, V_{GS} = 5V,$ | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 21.6 | — | ns | $R_{L} = 1.7\Omega, R_{g} = 6\Omega$ | |
| Turn-Off Fall Time | t _F | — | 5.3 | — | ns | | |

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

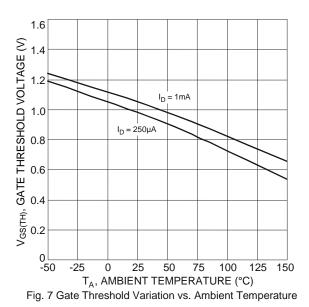


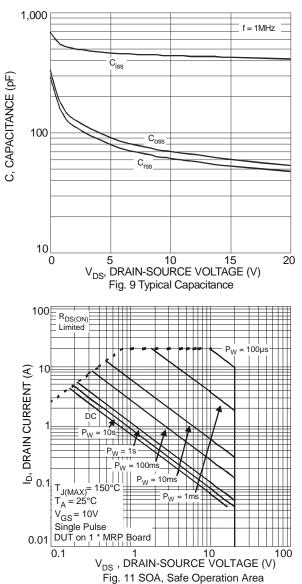
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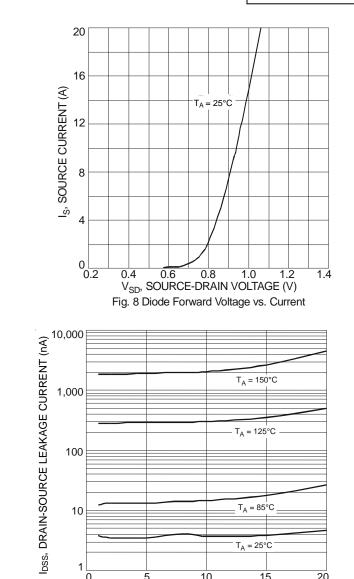


DMG3420UQ Document number: DS41788 Rev. 1 - 2 Downloaded from Arrow.com.









5 10 15 V_{DS}, DRAIN-SOURCE VOLTAGE (V) 20 Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

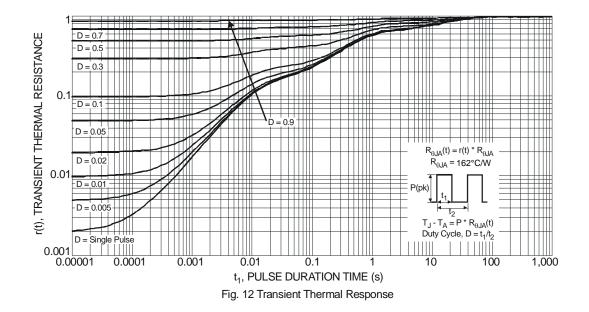
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 $T_A = 85^{\circ}C$

T_A = 25°C



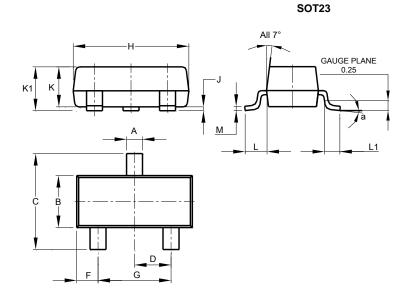






Package Outline Dimensions

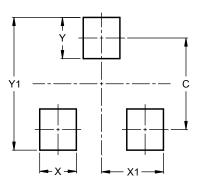
Please see http://www.diodes.com/package-outlines.html for the latest version.



| SOT23 | | | | | |
|----------------------|-------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 0.37 | 0.51 | 0.40 | | |
| В | 1.20 | 1.40 | 1.30 | | |
| С | 2.30 | 2.50 | 2.40 | | |
| D | 0.89 | 1.03 | 0.915 | | |
| F | 0.45 | 0.60 | 0.535 | | |
| G | 1.78 | 2.05 | 1.83 | | |
| н | 2.80 | 3.00 | 2.90 | | |
| J | 0.013 | 0.10 | 0.05 | | |
| К | 0.890 | 1.00 | 0.975 | | |
| K1 | 0.903 | 1.10 | 1.025 | | |
| L | 0.45 | 0.61 | 0.55 | | |
| L1 | 0.25 | 0.55 | 0.40 | | |
| М | 0.085 | 0.150 | 0.110 | | |
| а | 0° | 8° | | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



 Dimensions
 Value (in mm)

 C
 2.0

 X
 0.8

 X1
 1.35

 Y
 0.9

 Y1
 2.9

SOT23



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